3407/H

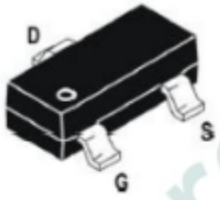
P-Channel Trench Power MOSFET

Features

- Extremely Low RDS(on):
- Typ. RDS(on) = 39mΩ @VGS=-10V, Id=-4A
- Good stability and uniformity
- 100% avalanche tested
- Excellent package for good heat dissipation

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Marking and Pin Assignment



SOT23-3

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Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Units
VDS	Drain-Source Voltage	-30	V
ID	Drain Current - Continuous (TC= 25°C),	-4	A
	Continuous (TC= 100°C)	-2.5*	A
IDM	Drain Current - Pulsed (Note 1)	-16*	A
VGS	Gate-Source Voltage	± 20	V
EAS	Single Pulsed Avalanche Energy (Note 2)	11	mJ
PD	Power Dissipation (TC = 25°C)- Derate above 25°C	1.36	W
		0.31	W/°C
TJ ,Tstg	Operating and Storage Temperature Range	-55 to +150	°C

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